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APPLICATION NO.	F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/504,782	,	02/15/2000	Masahiro Kume	0819-337	8307
22204	7590	06/02/2005		EXAMINER	
NIXON PE		•	FLORES RUIZ, DELMA R		
401 9TH ST SUITE 900	KEEI, N	w		ART UNIT	PAPER NUMBER
WASHINGT	TON, DC	20004-2128	2828		
				DATE MAILED: 06/02/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	(an)				
	09/504,782	KUME ET AL.	Oh				
Office Action Summary	Examiner	Art Unit					
	Delma R. Flores Ruiz	2828					
The MAILING DATE of this communication ap Period for Reply	pears on the cover sheet with the	correspondence addre	ss				
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a rep. If NO period for reply is specified above, the maximum statutory period. - Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	136(a). In no event, however, may a reply be to bly within the statutory minimum of thirty (30) da will apply and will expire SIX (6) MONTHS from the, cause the application to become ABANDON	imely filed ys will be considered timely. n the mailing date of this comm ED (35 U.S.C. § 133).	unication.				
Status							
1) Responsive to communication(s) filed on 16 f	<u>March 2005</u> .						
	s action is non-final.						
3) Since this application is in condition for allows	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
closed in accordance with the practice under	closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims							
4) Claim(s) <u>1-6, 24, 25</u> is/are pending in the app	lication.						
4a) Of the above claim(s) is/are withdra							
5)⊠ Claim(s) <u>4-6, 25</u> is/are allowed.							
6)⊠ Claim(s) <u>1-3 and 24</u> is/are rejected.							
7) Claim(s) is/are objected to.							
8) Claim(s) are subject to restriction and/	or election requirement.						
Application Papers							
9)☐ The specification is objected to by the Examin	er.						
	☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.						
Applicant may not request that any objection to the	e drawing(s) be held in abeyance. So	ee 37 CFR 1.85(a).					
Replacement drawing sheet(s) including the correct	ction is required if the drawing(s) is o	bjected to. See 37 CFR	1.121(d).				
11)☐ The oath or declaration is objected to by the E	xaminer. Note the attached Offic	e Action or form PTO-	152.				
Priority under 35 U.S.C. § 119							
12) ☐ Acknowledgment is made of a claim for foreig a) ☐ All b) ☐ Some * c) ☐ None of:	n priority under 35 U.S.C. § 119(a	a)-(d) or (f).					
1. Certified copies of the priority documen	its have been received.						
2. Certified copies of the priority documen	its have been received in Applica	tion No					
3. Copies of the certified copies of the price	ority documents have been receiv	ed in this National Sta	ige				
application from the International Burea	au (PCT Rule 17.2(a)).						
* See the attached detailed Office action for a lis	t of the certified copies not receive	ved.					
Attachment(s)	_						
1) Notice of References Cited (PTO-892)	4) Interview Summar	y (PTO-413) Pata					
 Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08 	Paper No(s)/Mail (5) Notice of Informal	Patent Application (PTO-15	2)				
Paper No(s)/Mail Date	6) Other:	· •					

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quótation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1 – 3 and 24 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sverdlov (6,455,337) in view of SAKAI, SHIRO (JP 09232627).

Regarding claims 1 – 3, and 24, Sverdlov discloses a semiconductor laser device (see Fig. 1, Character 10) comprising; a first cladding (see Fig. 1, Character 16) layer, which is mace of a nitride semiconductor of a first conductivity type (see Fig. 1, Character 18) and is formed over a substrate (see Fig. 1, Character 12); an active layer (see Fig. 1, Character 20), which is mode of, which is made In_y Ga_{1-y}N layer and is formed over the first cladding layer; and a second cladding (see Fig. 1, Character 24) layer, which is made of still another nitride semiconductor of a second conductivity type (see Fig. 1, Character 22)

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and is formed over the active layer (see Figs. 1 – 7, Abstract, Column 2, lines 43 – 67, Column 4, lines 11 – 65). The $In_xGa_{1-x}N$ layer and is formed in contact with the first cladding layer and substrate (see Figs. 1 – 7, Abstract, Column 2, lines 43 – 67, Column 4, lines 11 – 65).

Sverdlov discloses the claimed invention except for Inx Ga1-xN layer of the first conductivity type is formed between the substrate and the first cladding layer and $x \ge y$ in the composition. SAKAI teaches providing his device with a wherein In_x Ga_{1-x}N layer of the first conductivity type is formed between the substrate and the first cladding layer and $x \ge y$ in the composition on In with semiconductor device for the purpose of conductive a specific area and provided to easily grow an indium-containing compound layer like an In_xAl_yGa_{1-x-y}N layer, by growing In_xGa_{1-x}N as a buffer layer so that mole density of indium is easily increased or decreased. It would have been obvious at the time of applicant's invention, to combine SAKAI of teaching a In_x Ga_{1-x}N layer of the first conductivity type is formed between the substrate and the first cladding layer and $x \ge y$ in the composition on In with semiconductor device because It would have been obvious to one having ordinary skill in the art at the time the invention was made to In_x Ga_{1-x}N layer of the first conductivity type is formed between the substrate and the first cladding layer and $x \ge y$ in the composition on In (Abstract), since it has been held to be within the general skill of a worker in the art to select a known material on the basis of its suitability for the intended use as a matter of obvious design choice. In re Leshin, 125 USPQ 416.

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Allowable Subject Matter

The following is an examiner's statement of reasons for allowance: claim 4 has been allowed over the prior art because they fail to teach a semiconductor laser device comprising; a first cladding layer, which is made of a nitride semiconductor of a first conductivity type and is formed over substrate; an active layer, which is made of $In_yGa_{1-y}N$ and is formed over the first cladding layer; a second cladding layer, which is made of still another nitride semiconductor of a second conductivity type and is formed over the active; an electrode formed over the second cladding layer, and an $In_xGa_{1-x}N$ of the first conductivity type is formed between the second cladding layer and electrode, wherein 0 < x < 1, 0 < y < 1 and x > y in the composition of In.

Claims 5 – 6 and 25 has been found allowable due to their dependency on claim 4.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reason for Allowance".

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Response to Arguments

Applicant's arguments with respect to claims 1 - 6 and 24 – 25 have been considered but are moot in view of the new ground(s) of rejection. Applicants amendments raised new issues that made necessary the new art to be applied and therefore, the arguments presented against Sverdlov are said to be moot due to the new grounds of rejection. Applicant's amendments have been fully addressed by the above presented rejection

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Delma R. Flores Ruiz whose telephone number is (571) 272-1940. The examiner can normally be reached on M - F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Min Sun Harvey can be reached on (571) -272-1835. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available

through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Delma R. Flores Ruiz

Examiner Art Unit 2828

DRFR/MH' October 31, 2004 Min Sun Harvey
Supervisor Patent Examiner
Art Unit 2828